



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/728,193	11/30/2000	Etsuo Morita	09792909-4714	4426

7590 01/10/2005

SONNENSCHN NATH & ROSENTHAL
80th Floor-Sears Tower
233 S. Wacker Drive
Chicago, IL 60606

EXAMINER

SONG, MATTHEW J

ART UNIT	PAPER NUMBER
----------	--------------

1765

DATE MAILED: 01/10/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

12

Office Action Summary

Application No.

09/728,193

Applicant(s)

MORITA, ETSUO

Examiner

Matthew J Song

Art Unit

1765

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 12 October 2004.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1,2,4-20 and 23-26 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1,2,4-20 and 23-26 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1, 2, 4-20 and 23-26 are rejected under 35 U.S.C. 103(a) as being unpatentable over Pribat et al (US 4,952,526) or Tsuda et al (US 6,294,440) in view of Natsume (US 5,672,520).

Pribat et al discloses a wafer **1** made of GaAs or InP (claim 14), this reads on applicant's basal body, depositing a dielectric thin layer **2** of silicon nitride or silica (claim 12-13), where excellent deposition selectivity can be obtained between GaAs and a silicon nitride film by plasma assisted CVD (claim 16-17) (col 10, ln 1-35) with a thickness between 5×10^{-2} and a few micrometers, etching a set of bands **23,24** (claim 2 and 7) on the dielectric using means known to those skilled in the art such as photolithography or wet or dry chemical attack (col 4, ln 50-60), where the bands **23,24** have a width of 0.5 to a few microns and being spaced out at distances of some microns to several hundred microns, thus periodically baring the substrate (col 10, ln 50-67 and col 11, ln 1-10 and Figs 23-24). Pribat et al also discloses a deposition of a thin film of III-V compound is deposited on the preceding structure by MOCVD, with a thickness of a few hundred angstroms to a few microns and depositing a second layer of dielectric, with a thickness of a few hundred angstroms to a few micrometers (col 11, ln 11-38 and Fig 26). Pribat et al also discloses apertures are etched in a second layer of the dielectric and the apertures are offset with

Art Unit: 1765

respect to the previous ones and the offset can vary from some micrometers to some hundreds of micrometers, this reads on applicant's forming patterns at least partly overlies one another and at least partly do not overlies one another. Pribat et al also discloses III-V polycrystalline material is removed by chemical attack through the apertures, this reads on applicant's forming an indentation (claim 16-19) so as to bare the monocrystalline seed through the apertures and growing a thin layer of monocrystalline III-V material between the dielectric layers and the upper dielectric is removed throughout the surface of the wafer so as to obtain a monocrystalline thin layer of semiconductor (claim 17) (col 11, ln 39-67 and Fig 27). Pribat et al also discloses repeating the disclosed method to obtain a stacking shown in Fig 14 (claims 16-19) (col 12, ln 1-25 and Figs 22-31). Pribat et al discloses a base layer **32** in Fig 31 (claims 11 and 16-19). Pribat et al also discloses a first pattern of dielectric material **50** and **51** with different lengths than a second pattern of dielectric material **20** and **21** in Fig 19.

Tsuda et al discloses a GaN layer **101**, this reads on applicant's base layer, is grown to a thickness of about 4 micrometers on a sapphire substrate **100** (claim 14) is placed in a growth chamber and a first patterned mask made of SiO₂ (claim 12-13) is formed on the GaN layer **101** by sputtering (claim 15) and the SiO₂ film is patterned to a periodic strip with a width of about 7 micrometers and a pitch of about 10 micrometers by conventional photolithography method, whereby a first SiO₂ mask **102** is formed (col 7, ln 20-45). Tsuda et al also discloses a GaN crystal film **103** is grown by Metal organic vapor phase epitaxy (MOVPE) to a thickness of about 3 micrometers and a forming a second mask on the GaN film **103**. Tsuda et al also discloses the second mask film **104** is a SiO₂ film with a thickness of about 200 nm with a periodic strip pattern (claim 2 and 7) with a width of about 8 micrometers and a pitch of about 10

Art Unit: 1765

micrometers is formed by a photolithography method and forming a GaN single crystal film **105** thereon by MOVPE (col 7, ln 46-67 and col 8, ln 1-30 and Fig 1). Tsuda et al also discloses it is important to select a relationship between the size of each opening of the first mask and the stripe width of the second mask, depending upon required characteristics of a light-emitting device, this reads on applicant's pitch of pattern elements (col 8, ln 31-65). Tsuda et al also discloses a semiconductor substrate including a sapphire substrate can also be used as a substrate, where a sapphire substrate may be peeled off from a semiconductor structure by grinding or etching and the remaining structure can be used as a substrate (claims 20 and 24) (col 22, ln 2-60).

Pribat et al or Tsuda et al does not disclose the pitch of pattern elements of one of the plurality of patterns and pitch of pattern elements of another of the plurality of patterns are different from each other.

In a method of checking alignment accuracy in photolithography, Natsume teaches three alignment check patterns **10, 20 and 100** are used. Natsume teaches alignment check pattern **10** consists of seven rectangular pattern elements, which are arranged parallel to each other in a row at a constant pitch q . Natsume also teaches alignment check pattern **100** consist of seven rectangular pattern elements which are arranged parallel to each other at a constant pitch p and pitch p differs from the pitch q of the pattern elements of alignment check patterns **10, 20** (col 3, ln 1-50). Natsume also teaches in a composite layout, the underlying check patterns **10, 20** and each of the pattern elements of the overlying pattern **100** partly overlaps both a pattern elements of the first and second check pattern (col 3, ln 51-67). It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify Tsuda et al or Pribat et al's method

Art Unit: 1765

of forming patterns using photolithography with Natsume's method of checking the alignment in photolithography using pattern elements with different pitches to check the alignment of the patterns (col 2, ln 40-55).

Referring to claim 4, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume does not teach the claimed relationship between the pitch of pattern elements. It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume to select any proportion of pitches that would produce a desired alignment because Natsume does not restrict the ratio of pitches (col 4, ln 40-55). In the absence of unexpected results, any ratio of pitches would have been obvious.

Referring to claims 5-6, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches using patterns with different lengths **13, 14** ('520 Fig 1).

Referring to claim 7, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches stripes.

Referring to claim 8-9, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches a region where the pattern element **101** does not overlie pattern elements **10,20** in Figure 2(A) of Natsume.

Referring to claim 10-15, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches using SiO₂ mask on a sapphire substrate to grow GaN ('440 col 7, ln 20-67).

Referring to claim 16-19, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches etching and using a masking material.

Art Unit: 1765

Referring to claim 20, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches removing the substrate ('440 col 22, ln 10-55).

Referring to claim 23-26, the combination of Tsuda et al and Natsume or the combination of Pribat et al and Natsume teaches using a plurality of patterns with different pitches ('520 col 3, ln 1-67).

Response to Arguments

3. Applicant's arguments, see page 6 of the appeal brief, filed 10/12/2004, with respect to Tsuda et al have been fully considered and are persuasive. The rejection of claims 1, 2, 4, 7, 11-15, and 23-26 has been withdrawn. Tsuda teaches the width of spacing and the width of the stripes can be changed, which are the elements of pitch. However, Tsuda et al does not teach patterns with a different pitch.
4. Applicant's arguments, see page 4 of the appeal brief, filed 10/12/2004, with respect to Pribat et al have been fully considered and are persuasive. The rejection of claims 1, 2, 4, 7, 11-20 and 23-24 has been withdrawn. Pribat teaches the width of spacing and the width of the stripes can be changed, which are the elements of pitch. However, Pribat does not teach patterns with a different pitch.
5. Applicant's arguments, see page 11 of the appeal brief, filed 10/12/2004, with respect to Fleming have been fully considered and are persuasive. The rejection of claims 1, 4-6 and 8-10 has been withdrawn. Fleming teaches the patterns with different shapes, sizes and orientation can

Art Unit: 1765

be used, which are elements of pitch. However, Fleming does not teach patterns with a different pitch.

6. Applicant's arguments with respect to claims 1, 2, 4-20 and 23-26 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Gardner et al (US 6,051,876) teaches a plurality of patterns **152** having different spacing and sizes, which reads on applicants' different pitch, in Figures 1B and 1C

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew J Song whose telephone number is 571-272-1468. The examiner can normally be reached on M-F 9:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 1765

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Matthew J Song
Examiner
Art Unit 1765

MJS
January 2, 2005

NADINE G. NORTON
SUPERVISORY PATENT EXAMINER

